

## Electrostatic Discharged Protection Devices (ESD) Data Sheet

### Description

Brightking's UDT23AXXL01 series are ultra low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by electrostatic discharge (ESD), cable discharge events(CDE) and electrical fast transients(EFT).The series has a maximum capacitance of only 1.2pF. This means it can be used on circuits operating in excess of 3GHz without signal attenuation.

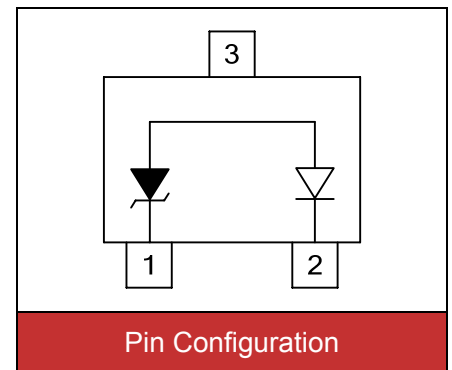


Contact : ±8kV  
Air : ±15kV



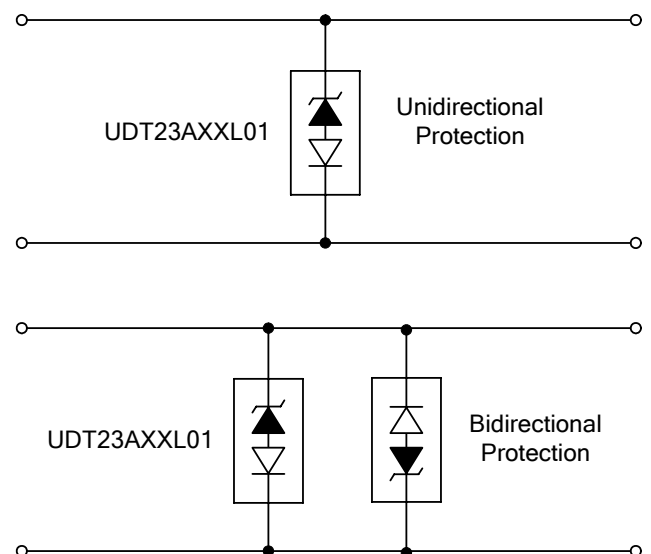
### Features

- IEC61000-4-2 ESD 15KV Air, 8KV contact compliance
- SOT-23 surface mount package
- Protects one high speed data line
- Peak power dissipation of 400W under 8/20μs waveform
- Working voltage: 3.3V, 5V, 12V, 15V and 24V
- Low leakage current
- Ultra low capacitance and clamping voltage
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020



### Applications

- HDMI interface protection
- Mobile display digital interface
- RF/Antenna circuits
- USB 2.0 & Firewire ports
- GaAs photodetector protection
- HBT power Amp protection
- Infiniband transceiver protection



**Maximum Ratings**

Rating	Symbol	Value	Unit
Peak pulse power (tp=8/20μs waveform)	P <sub>PP</sub>	400	W
ESD voltage (Contact discharge)	V <sub>ESD</sub>	±8	kV
ESD voltage (Air discharge)		±15	
Storage & operating temperature range	T <sub>STG</sub> , T <sub>J</sub>	-55~+150	°C

**Electrical Characteristics (T<sub>J</sub>=25°C)**

UDT23A03L01 (Marking: B SJ)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V <sub>RWM</sub>				3.3	V
Reverse breakdown voltage	V <sub>BR</sub>	I <sub>BR</sub> =1mA	4			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =3.3V			50	μA
Clamping voltage (tp=8/20μs)	V <sub>C</sub>	I <sub>PP</sub> =1A			8	V
Clamping voltage (tp=8/20μs)	V <sub>C</sub>	I <sub>PP</sub> =5A			10	V
Off state junction capacitance	C <sub>J</sub>	0Vdc, f=1MHz Between I/O pins and GND			1.2	pF

UDT23A05L01 (Marking: B SK)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V <sub>RWM</sub>				5	V
Reverse breakdown voltage	V <sub>BR</sub>	I <sub>BR</sub> =1mA	6			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =5V			5	μA
Clamping voltage (tp=8/20μs)	V <sub>C</sub>	I <sub>PP</sub> =1A			9.5	V
Clamping voltage (tp=8/20μs)	V <sub>C</sub>	I <sub>PP</sub> =5A			12	V
Off state junction capacitance	C <sub>J</sub>	0Vdc, f=1MHz Between I/O pins and GND			1.2	pF

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ )**
**UDT23A12L01 (Marking: B SL)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				12	V
Reverse breakdown voltage	$V_{BR}$	$I_{BR}=1\text{mA}$	13.3			V
Reverse leakage current	$I_R$	$V_R=12\text{V}$			1	$\mu\text{A}$
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=1\text{A}$			19	V
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=5\text{A}$			24	V
Off state junction capacitance	$C_J$	0Vdc, f=1MHz Between I/O pins and GND			1.2	pF

**UDT23A15L01 (Marking: B SM)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				15	V
Reverse breakdown voltage	$V_{BR}$	$I_{BR}=1\text{mA}$	16.7			V
Reverse leakage current	$I_R$	$V_R=15\text{V}$			1	$\mu\text{A}$
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=1\text{A}$			24	V
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=5\text{A}$			30	V
Off state junction capacitance	$C_J$	0Vdc, f=1MHz Between I/O pins and GND			1.2	pF

**UDT23A24L01 (Marking: B SN)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				24	V
Reverse breakdown voltage	$V_{BR}$	$I_{BR}=1\text{mA}$	26.7			V
Reverse leakage current	$I_R$	$V_R=24\text{V}$			1	$\mu\text{A}$
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=1\text{A}$			43	V
Clamping voltage ( $t_p=8/20\mu\text{s}$ )	$V_C$	$I_{PP}=5\text{A}$			55	V
Off state junction capacitance	$C_J$	0Vdc, f=1MHz Between I/O pins and GND			1.2	pF

Typical Characteristics Curves

Figure 1. Power Derating Curve

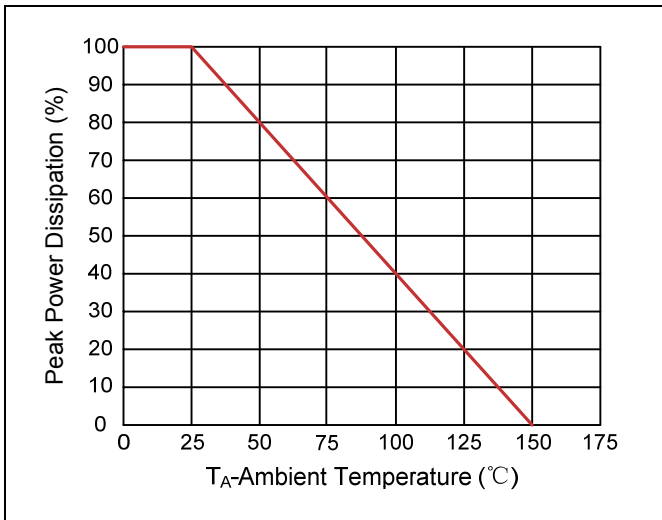


Figure 2. Pulse Waveforms

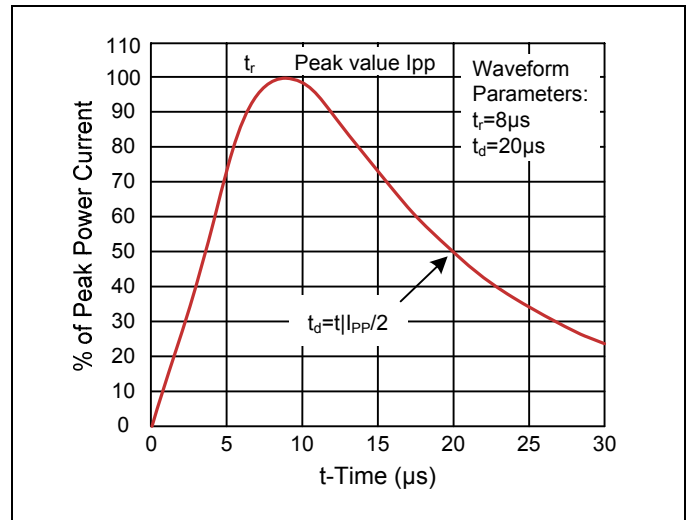


Figure 3. Non-Repetitive Peak Pulse vs. Pulse Time

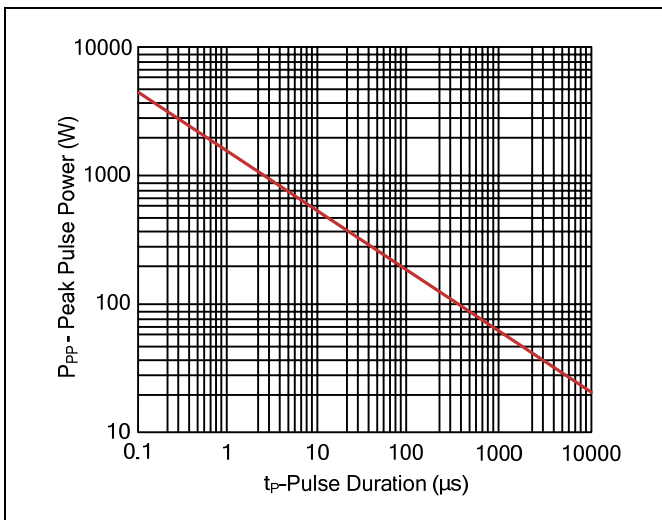
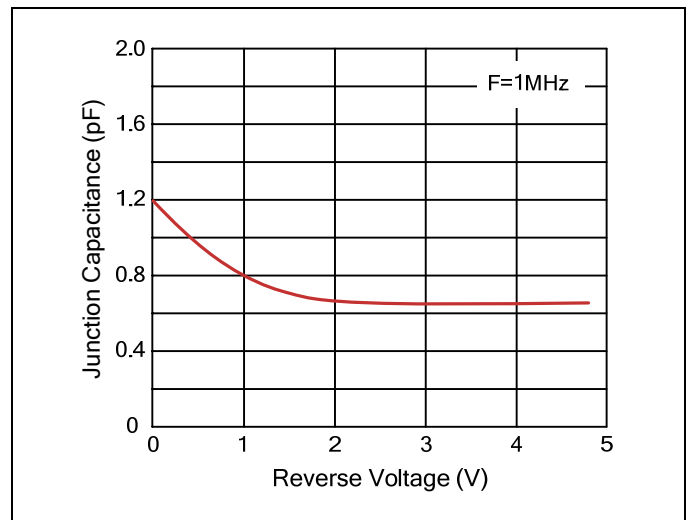
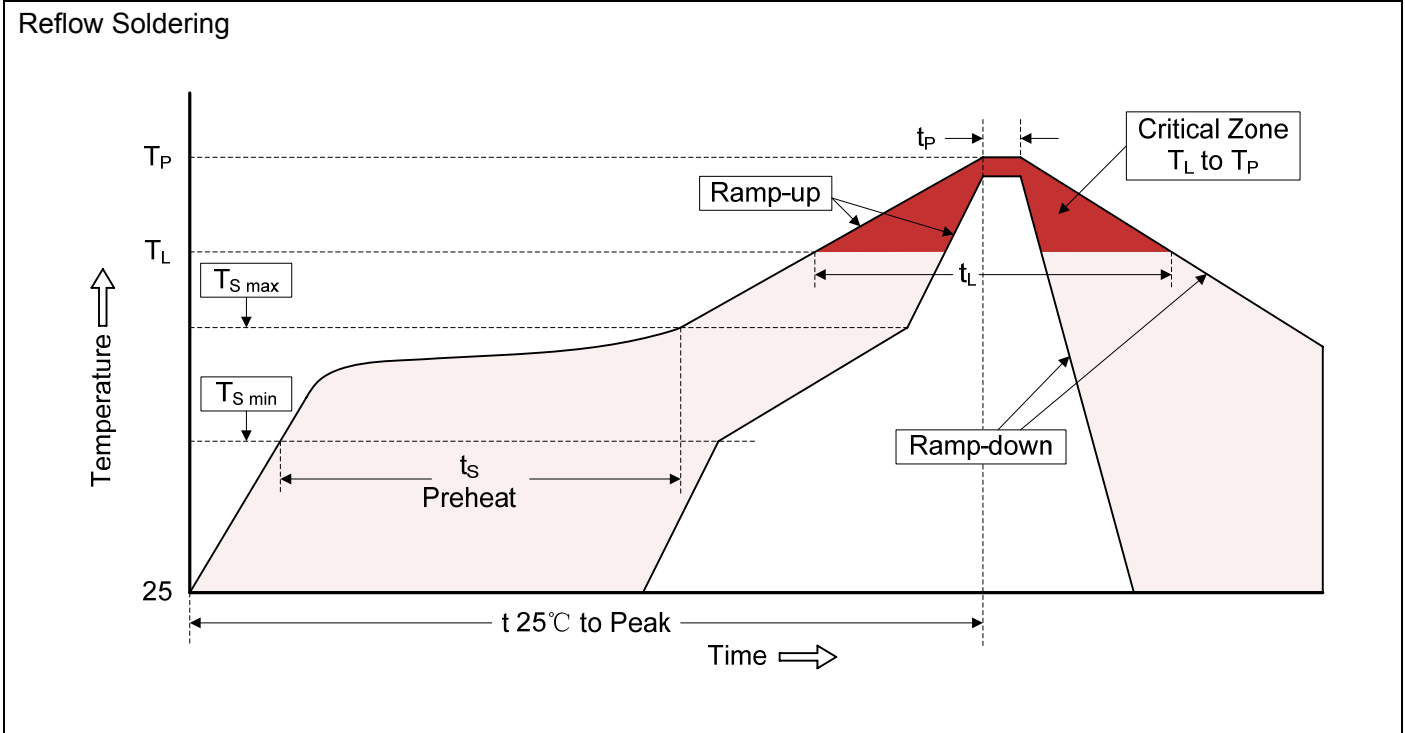


Figure 4. Capacitance vs. Reverse Voltage



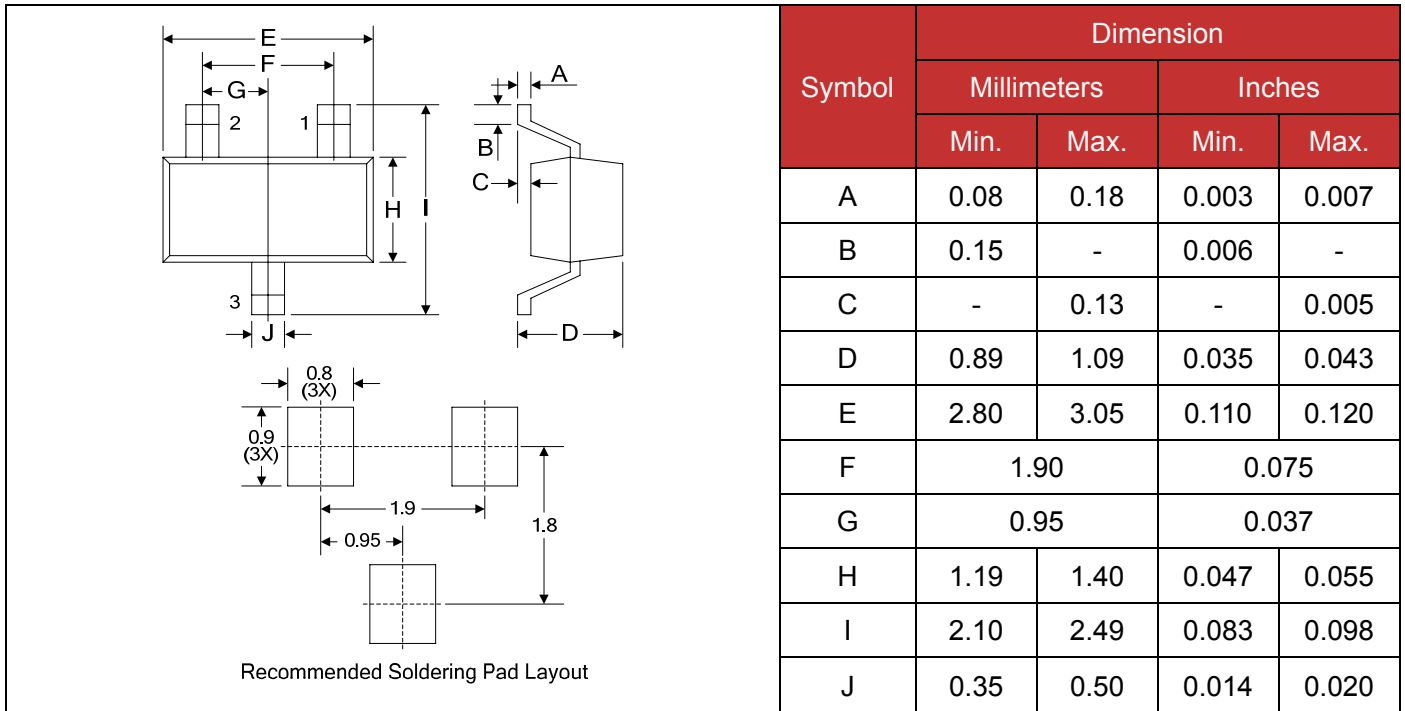
Recommended Soldering Conditions



Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	3°C/second max.
Preheat -Temperature Min ( $T_{S\ min}$ ) -Temperature Max ( $T_{S\ max}$ ) -Time (min to max) ( $t_s$ )	150°C 200°C 60-180 seconds
$T_{S\ max}$ to $T_L$ -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature ( $T_L$ ) -Time ( $t_L$ )	217°C 60-150 seconds
Peak Temperature ( $T_P$ )	260°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

**Dimensions (SOT-23)**



**Packaging**

